

BCR08AM-14A

Triac

Low Power Use

REJ03G1200-0200 Rev.2.00 Nov 30, 2007

Features

 $\bullet \quad I_{T\,(RMS)}:0.8\;A$ V_{DRM} : 700 V

• $I_{FGT I}$, $I_{RGT I}$, $I_{RGT III}$: 5 mA Planar Passivation Type

Outline

RENESAS Package code: PRSS0003EA-A (Package name: TO-92) 1. T₁ Terminal 2. T₂ Terminal 3. Gate Terminal

Applications

Washing machine, electric fan, air cleaner, other general purpose control applications

Maximum Ratings

Parameter	Symbol	Voltage class	Unit	
Faranieter	Symbol	14	Offic	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	700	V	
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	840	V	

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Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	0.8	Α	Commercial frequency, sine full wave 360° conduction, Tc = 67°C
Surge on-state current	I _{TSM}	8	A	60 Hz sinewave 1 full cycle, peak value, non-repetitive
I ² t for fusing	l ² t	0.26	A ² s	Value corresponding to 1 cycle of half wave 60 Hz, surge on-state current
Peak gate power dissipation	P_{GM}	1	W	
Average gate power dissipation	P _{G (AV)}	0.1	W	
Peak gate voltage	V_{GM}	6	V	
Peak gate current	I _{GM}	0.5	А	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	_	0.23	g	Typical value

Notes: 1. Gate open.

Electrical Characteristics

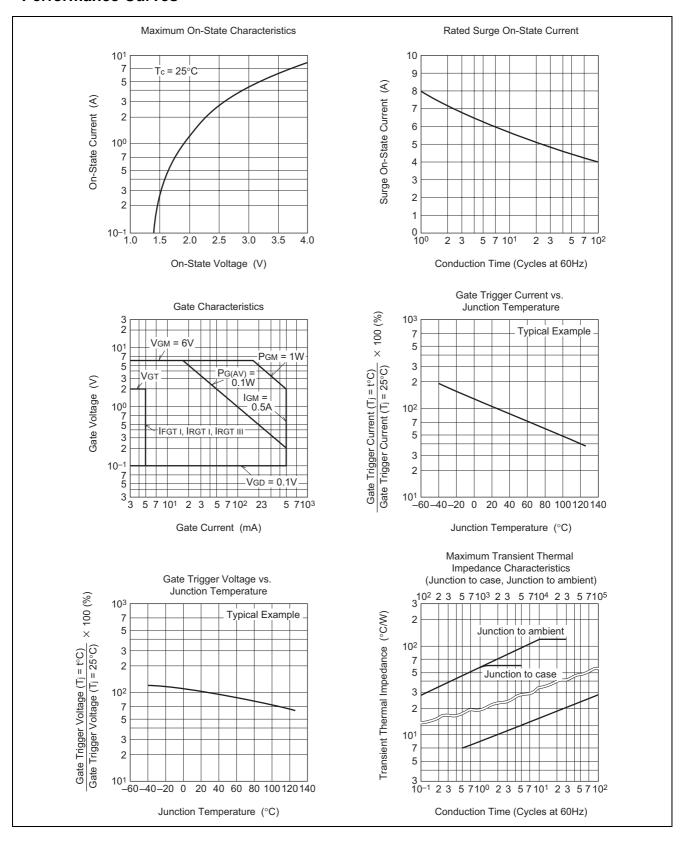
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions	
Repetitive peak off-state current		I _{DRM}	_	_	1.0	mA	Tj = 125°C, V _{DRM} applied	
On-state voltage		V_{TM}	_	_	2.0	V	$Tc = 25^{\circ}C$, $I_{TM} = 1.2 A$,	
							Instantaneous measurement	
Gate trigger voltage ^{Note2}	I	V_{FGTI}			2.0	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,	
	II	V_{RGTI}			2.0	V	$R_G = 330 \Omega$	
	III	V_{RGTIII}		_	2.0	V		
Gate trigger current ^{Note2}	I	I _{FGTI}			5	mA	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$	
		I_{RGTI}			5	mA	$R_G = 330 \Omega$	
	III	I_{RGTIII}	_	_	5	mA		
Gate non-trigger voltage		V_{GD}	0.1	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$	
Thermal resistance		R _{th (j-c)}			50	°C/W	Junction to case ^{Note3}	
Critical-rate of rise of off-stat commutating voltage Note4	е	(dv/dt)c	0.5	_	_	V/μs	Tj = 125°C	

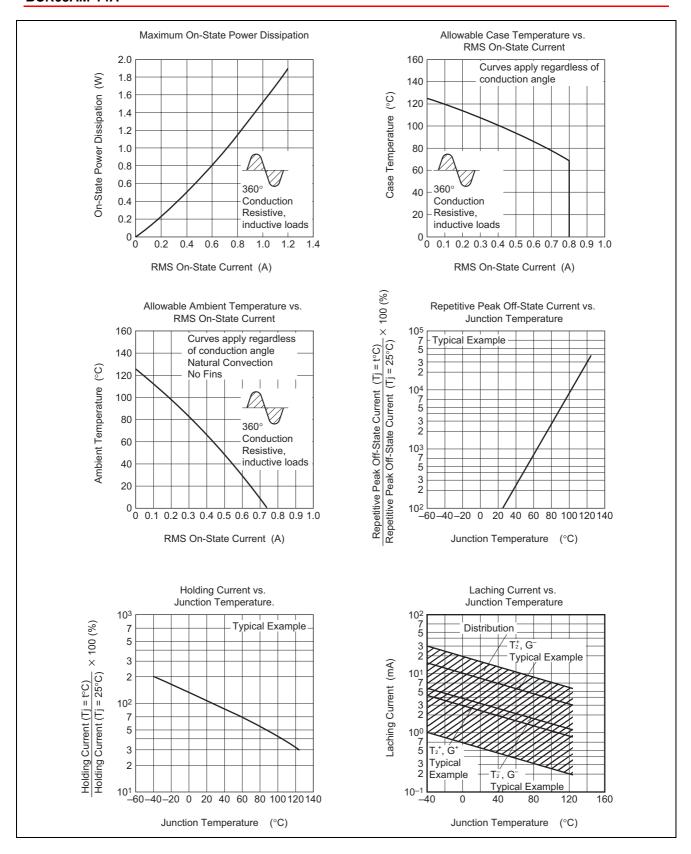
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

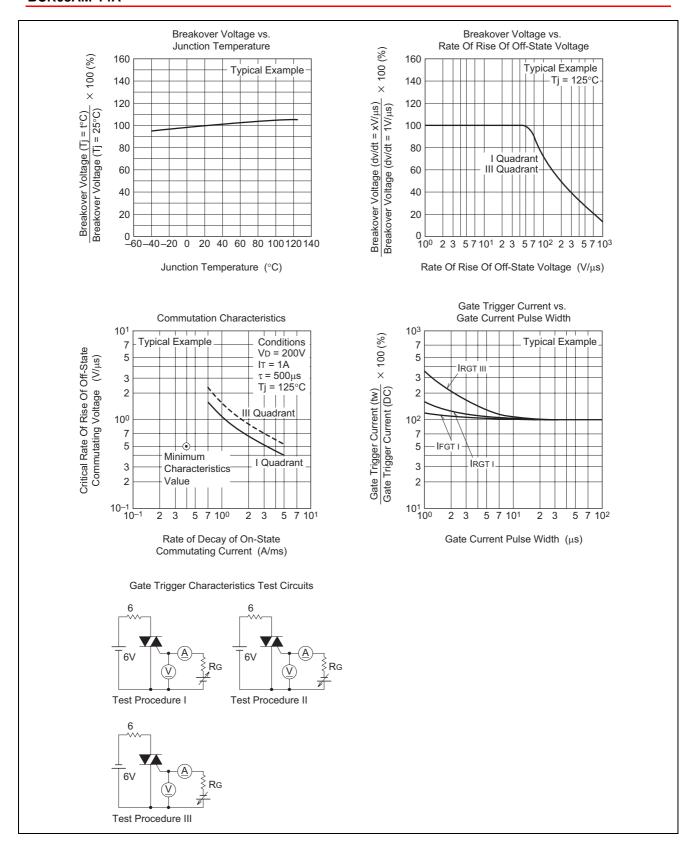
- 3. Case temperature is measured at the T_2 terminal 1.5 mm away from the molded case.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C	Supply → Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 0.4 A/ms	Main Current → Time		
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage (dv/dt)c VD		

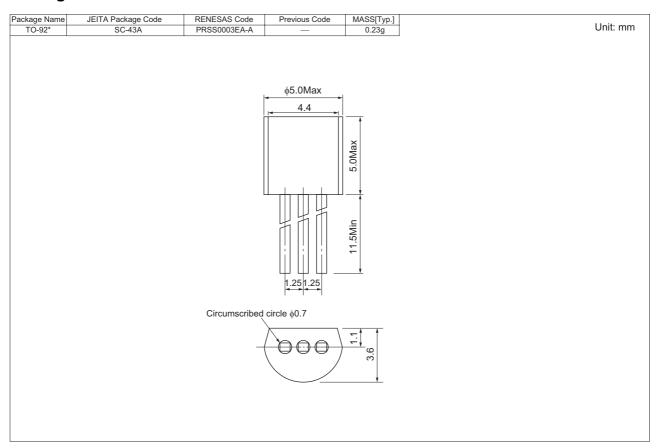
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	500	Type name	BCR08AM-14A
Lead form	Vinyl sack	500	Type name – Lead forming code	BCR08AM-14A-A6
Form A8	Taping	2000	Type name – TB	BCR08AM-14A-TB

Note: Please confirm the specification about the shipping in detail.

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- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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